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# TABLE OF CONTENTS

KEYNOTE: The Reliability Challenge: New Materials in the New Millenium

Moore's Law Drive's a Discontinuity

*J.S. England and R.W. England* ..... 1

## MICROELECTROMECHANICAL SYSTEMS

Session Co-Chairs: William M. Miller and Sammy A. Kayali

Lifetime Estimates and Unique Failure Mechanisms of the Digital Micromirror Device (DMD)

*M.R. Douglass* ..... 9

Failure Modes in Surface Micromachined MicroElectroMechanical Actuators

*S.L. Miller, M.S. Rodgers, G. LaVigne, J.J. Sniegowski, P. Clews, D.M. Tanner, and K.A. Peterson* ..... 17

The Effect of Frequency on the Lifetime of a Surface Micromachined Microengine Driving a Load

*D.M. Tanner, W.M. Miller, W.P. Eaton, L.W. Irwin, K.A. Peterson, M.T. Dugger, D.C. Senft, N.F. Smith, P. Tangyuyong, and S.L. Miller* ..... 26

## DIELECTRICS

Session Co-Chairs: Bill Abadeer and Robin Degraeve

Enhanced Dielectric Breakdown Lifetime of Copper/Silicon Nitride/Silicon Dioxide Structure

*K. Takeda, K. Hinode, I. Oodake, N. Oohashi, and H. Yamaguchi* ..... 36

Switching behavior of the Soft Breakdown Conduction Characteristic in Ultra-thin (<5 nm)

Oxide MOS Capacitors

*E. Miranda, J. Suñé, R. Rodríguez, M. Nafria, and X. Aymerich* ..... 42

Disturbed Bonding States in SiO<sub>2</sub> Thin-Films and Their Impact on Time-Dependent

Dielectric Breakdown

*J.W. McPherson and H.C. Mogul* ..... 47

Deep-Trap SILC (Stress Induced Leakage Current) Model For Nominal and Weak Oxides

*S. Kamohara, D. Park, and C. Hu* ..... 57

Constant Current Charge-to-Breakdown: Still a Valid Tool to Study the Reliability of MOS Structures?

*T. Nigam, R. Degraeve, G. Groeseneken, M.M. Heyns, and H.E. Maes* ..... 62

Improvement of Gate Dielectric Reliability for p+ Poly MOS Devices Using Remote

PECVD Top Nitride Deposition on Thin Gate Oxides

*Y. Wu and G. Lucovsky* ..... 70

Trap Assisted Tunneling as a Mechanism of Degradation and Noise in 2-5 nm Oxides

*G.B. Alers, B.E. Weir, M.A. Alam, G.L. Timp, and T. Sorch* ..... 76

A New Algorithm for Transforming Exponential Current Ramp Breakdown Distributions into

Constant Current TDDB Space, and the Implications for Gate Oxide Q<sub>BD</sub> Measurement Methods

*N.A. Dumin* ..... 80

The Correlation of Highly Accelerated Q<sub>bd</sub> Tests to TDDB Life Tests for Ultra-Thin Gate Oxides

*Y. Chen, J.S. Suehle, C.-C. Shen, J.B. Bernstein, C.R. Messick, and P. Chaparala* ..... 87

## COMPOUND SEMICONDUCTORS

Session Co-Chairs: Anthony A. Immorlica, Jr. and Fausto Fantini

Early Variations of the Base Current in In/C-Doped GaInP/GaAs HBT's

*M. Borgarino, R. Plana, S. Delage, H. Blanck, F. Fantini, and J. Grafeuil* ..... 92

Degradation of InGaAs/InP Heterojunction Bipolar Transistors Under High Energy Electron Irradiation

*A. Bandyopadhyay, S. Subramanian, S. Chandrasekhar, and S.M. Goodnick* ..... 98

Dislocation Dynamics in Heterojunction Bipolar Transistor Under Current Induced Thermal Stress

*C.-T. Tsai and L.L. Liou* ..... 103

A Novel, High Resolution Non-Contact Channel Temperature Measurement Technique

*Q. Kim, B. Stark, and S.A. Kayali* ..... 108

## OPTOELECTRONICS

Session Chair: Daniel L. Barton

REDR-Based Kinetics for Line Defects Leading to Sudden Failures in 980 nm SL SQW InGaAs Laser Diodes <i>A. Borfiglio, M.B. Casu, M. Vanzi, F. Magistrali, M. Maini, and G. Salmini, .....</i>	113
Degradation of Single-Quantum Well InGaN Green Light Emitting Diodes Under High Electrical Stress <i>D.L. Barton, M. Osinski, P. Perlin, P.G. Eliseev, and J. Lee .....</i>	119

## FAILURE ANALYSIS

Session Co-Chairs: Kris Mohan and Steven J. Kirch

(Invited) A Reliability Study of Titanium Silicide Lines Using Micro-Raman Spectroscopy and Emission Microscopy <i>I. DeWolf, D.J. Howard, M. Rasras, A. Lauwers, K. Maex, G. Groeseneken, and H.E. Maes .....</i>	124
Backside Localization of Open and Shorted IC Interconnections <i>E.I. Cole Jr., P. Tangyunyong, and D.L. Barton .....</i>	129
Dynamics of Backside Wafer Level Microprobing <i>C.-L. Chiang and D.T. Hurley .....</i>	137
A New Failure Mechanism by Corrosion of Tungsten in a Tungsten Plug Process <i>S. Bothra, H. Sur, and V. Liang .....</i>	150
Cross-sectional Atomic Force Microscopy of Focused Ion Beam Milled Device <i>J.L. Ebel, C. Bozada, T.E. Schlesinger, C. Cerny, G. DeSalvo, R. Dettmer, J. Gillespie, T. Jenkins, K. Nakano, C. Pettiford, T. Quach, J. Sewell, G. Via, and R. Welch .....</i>	157
Nanoscale Electrical Characterization of Thin Oxides with Conducting Atomic Force Microscopy <i>A. Olbrich, B. Ebersberger, and C. Boit .....</i>	163
High-Resolution Current and Temperature Mapping of Electronic Devices Using Scanning Joule Expansion Microscopy <i>J. Varesi, S. Muenster, and A. Majumdar .....</i>	169

## HOT CARRIERS

Session Co-Chairs: Tom Kopley and Matt Wordman

Assessing Circuit-Level Hot-Carrier Reliability <i>W. Jiang, H. Le, J. Chung, T.E. Kopley, P.J. Marcoux, and C. Dai .....</i>	173
Effects of Advanced Processes on Hot Carrier Reliability <i>S. Aur, T. Grider, V. McNeil, T. Holloway, and R. Eklund .....</i>	180
Hot-Carrier Degradation Mechanism and Promising Device Design of nMOSFETs with Nitride Sidewall Spacer <i>Y. Sambonsugi and T. Sugii .....</i>	184
Effects of Halo Implant on Hot Carrier Reliability of Sub-Quarter Micron MOSFETs <i>A. Das, H. De, V. Misra, S. Venkatesan, S. Veeraraghavan, and M. Foisy .....</i>	189
Channel Coupling Imposed Tradeoffs on Hot-Carrier Degradation and Single Transistor Latch-up in SOI MOSFETs <i>F.L. Duan, D.E. Ioannou, W.C. Jenkins, H.L. Hughes, and S.T. Liu .....</i>	194
Comparison of Hot-Carrier Effects in Deep Submicron <i>n</i> - and <i>p</i> -Channel Partially- and Fully-Depleted Unibond and SIMOX MOSFETs <i>S.H. Renn, C. Raynaud, J.L. Pelloie, and F. Balestra .....</i>	203
Voltage Scaling and Temperature Effects on Drain Leakage Current Degradation in a Hot Carrier Stressed n-MOSFET <i>T. Wang, C.F. Hsu, L.P. Chiang, N.K. Zous, T.S. Chao, and C.Y. Chang .....</i>	209

## PACKAGING AND ASSEMBLY

Session Co-Chairs: Thomas M. Moore and Richard L. Shook

Method for Equivalent Acceleration of JEDEC/IPC Moisture Sensitivity Levels <i>R.L. Shook, B.T. Vaccaro, and D.L. Gerlach</i> .....	214
Critical Parameters for Reliable Surface Mounting of High Pincount Packages <i>B.L. Euzent, B. Kawanami and S. Lau</i> .....	220
Elimination of Bond-pad Damage Through Structural Reinforcement of Intermetal Dielectrics <i>M. Saran, R. Cox, C. Martin, G. Ryan, T. Kudoh, M. Kanasugi, J. Hortaleza, M. Ibnabdeljalil, M. Murtuza, D. Capistrano, R. Roderos, and R. Macaraeg</i> .....	225
The Evolution of Hydrogen from Plastic Molding Compound and Its' Effect on the Yield and Reliability of Ferroelectric Memories <i>E.M. Philofsky, C.R. Ostrander, and S.J. Hartman</i> .....	232
In-Situ Monitoring of Bond Degradation in Power IC's Under High Current Stress <i>B. Krabbenborg</i> .....	238
Thermal Resistance Degradation of Alloy Die Attached Devices During Thermal Cycling <i>J. Naderman, F.W. Ragay, D.G. de Vries, A. van Eck, and J. van de Water</i> .....	248
Influences of Fan-in/Fan-out Structure and Underfill Fillet on TCT Reliability of Flip Chip BGA <i>H. Shimoe, T. Iijima, T. Iiyama, K. Oyama, H. Taguchi, and Y. Hiruta</i> .....	254
Chip Scale Package (CSP) Solder Joint Reliability and Modeling <i>M. Amagai</i> .....	260

## LATCHUP/ESD

Session Co-Chairs: E. Ajith Amerasekera and James W. Miller

(Invited) Latchup in CMOS Technology <i>M.J. Hargrove, S.H. Voldman, R. Gauthier, J. Brown, K. Duncan, and W. Craig</i> .....	269
A Study of ESD-Induced Latent Damage in CMOS Integrated Circuits <i>Y. Huh, M.G. Lee, J.S. Lee, H.C. Jung, T. Li, D.-H. Song, Y.J. Lee, J.M. Hwang, Y.K. Sung, and S.M. Kang</i> .....	279
High Current Effects in Silicide Films for Sub-0.25 µm VLSI Technologies <i>K. Banerjee, A. Amerasekera, J.A. Kitl, and C. Hu</i> .....	284
High-Current Transmission Line Pulse Characterization of Aluminum and Copper Interconnects for Advanced CMOS Semiconductor Technologies <i>S.H. Voldman, R. Gauthier, D. Reinhart, and K. Morrisseau</i> .....	293
Antenna Protection Strategy for Ultra-thin Gate MOSFETs <i>S. Krishnan and A. Amerasekera</i> .....	302
Reduction of Plasma-Induced Gate Oxide Damage Using Low-Energy Large-Mass Ion Bombardment in Gate-Metal Sputtering Deposition <i>T. Ushiki, M.C. Yu, K. Kawai, T. Shinohara, K. Ino, M. Morita, and T. Ohmi</i> .....	307
Characterization of Plasma Charging Damage in Ultrathin Gate Oxides <i>H.-C. Lin, M.-F. Wang, C.-C. Chen, S.-K. Hsien, C.-H. Chien, T.-Y. Huang, C.-Y. Chang, and T.-S. Chao</i> .....	312

## INTERCONNECT AND METALLIZATION

Session Co-Chairs: William R. Hunter and Paul Ho

Stress-Induced Voiding in Stacked Tungsten Via Structure <i>S. Domae, H. Masuda, K. Tateiwa, Y. Kato, and M. Fujimoto</i> .....	318
Statistics of Microstructure for Via Metallization and Implication for Electromigration Reliability <i>H. Toyoda, P.-H. Wang, and P.S. Ho</i> .....	324
Ti Layer Thickness Dependence on Electromigration Performance of Ti/AlCu Metallization <i>M. Hosaka, T. Kouno, Y. Hayakawa, H. Niwa, and M. Yamada</i> .....	329

Effect of H <sub>2</sub> O Partial Pressure and Temperature During Ti Sputtering on Texture and Electromigration in AlSiCu/Ti/TiN/Ti Metallization <i>T. Yoshida, S. Hashimoto, Y. Mitsushima, T. Ohwaki, and Y. Taga</i>	335
Cu Damascene Interconnects with Crystallographic Texture Control and its Electromigration Performance <i>K. Abe, Y. Harada, and H. Onoda</i>	342
Effect of VLSI Interconnect Layout on Electromigration Performance <i>E.M. Atakov, T.S. Sriram, D. Dunnell, and S. Pizzanello</i>	348
Full-Chip Reliability Analysis <i>S. Rochel, G. Steele, J.R. Lloyd, S.Z. Hussain, and D. Overhauser</i>	356
<b>DEVICE AND PROCESS</b>	
Session Co-Chairs: Timothy A. Rost and Guido Groeseneken	
A Comparative Study of Leakage Mechanism of Co and Ni Salicide Processes <i>K. Goto, J. Watanabe, T. Sukegawa, A. Fushida, T. Sakuma, and T. Sugii</i>	363
Impact of Screening of Latent Defects at Electrical Test on the Yield-Reliability Relation and Application to Burn-In Elimination <i>J.A. van der Pol, E.R. Ooms, T. van 't Hof, and F.G. Kuper</i>	370
Extended Data Retention Process Technology for Highly Reliable FLASH EEPROMs of 10 <sup>6</sup> to 10 <sup>7</sup> W/E Cycles <i>F. Arai, T. Maruyama, and R. Shirota</i>	378
Hot-Electron Degradation and Unclamped Inductive Switching in Sub-micron 60-V Lateral DMOS <i>M.S. Shekar, R.K. Williams, M. Cornell, M.-Y. Luo, and M. Darwish</i>	383
<i>Biographies</i>	393
<i>Index to Paper #</i>	406
<i>1998 Committees</i>	407
<i>1996 Paper Awards</i>	412
<i>Exceptional Service Award</i>	414
<i>1998 Tutorial Program</i>	415
<i>1998 Equipment Demonstrations</i>	419